L Number	Hits	Search Text	DB	Time stamp
-	79330	silicon adj nitride	USPAT;	2004/09/10
-	5648	"Si.sub.3N.sub.4"	US-PGPUB USPAT;	16:53 2004/09/10
-	959	Si3N4	US-PGPUB USPAT;	16:54 2004/09/10
-	346	"Si.sub.xN.sub.y"	US-PGPUB USPAT;	16:54 2004/09/10
-	96	SixNy	US-PGPUB USPAT;	16:54 2004/09/10
-	78856	chemical adj vapor adj deposit\$3	US-PGPUB USPAT; US-PGPUB	16:55 2004/09/10
-	77927	CVD	USPAT; US-PGPUB	16:56 2004/09/10
-	571	rapid adj thermal adj ((chemical adj vapor adj deposit\$3) or CVD)	USPAT; US-PGPUB	16:57 2004/09/10 16:57
-	171	remote adj plasma adj enhanced adj ((chemical adj vapor adj deposit\$3) or CVD)	USPAT; US-PGPUB	2004/09/10 16:58
-	313	atomic adj layer adj ((chemical adj vapor adj deposit\$3) or CVD)	USPAT; US-PGPUB	2004/09/10 16:58
-	815	thermal adj nitridation	USPAT; US-PGPUB	2004/09/10
-	435	plasma adj nitridation	USPAT; US-PGPUB	2004/09/10 16:59
-	0	((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or SixNy) same (rapid	USPAT; US-PGPUB	2004/09/10 17:00
		adj thermal adj ((chemical adj vapor adj deposit\$3) or CVD)) same (remote adj plasma adj enhanced adj ((chemical adj vapor adj deposit\$3) or CVD)) same (atomic adj layer adj ((chemical adj vapor adj deposit\$3) or CVD)) same (thermal adj nitridation) same (plasma adj nitridation)		11100
-	0	((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or SixNy) same (rapid adj thermal adj ((chemical adj vapor adj deposit\$3) or CVD)) same (remote adj plasma adj enhanced adj ((chemical adj vapor adj deposit\$3) or CVD)) same (atomic adj layer adj ((chemical adj vapor adj deposit\$3) or CVD))	USPAT; US-PGPUB	2004/09/10 17:00
-	594	((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or SixNy) same ((rapid adj thermal adj ((chemical adj vapor adj deposit\$3) or CVD)) or (remote adj plasma adj enhanced adj ((chemical adj vapor adj deposit\$3) or CVD)) or (atomic adj layer adj ((chemical adj vapor adj deposit\$3) or CVD)) or (thermal adj nitridation) or (plasma adj nitridation))	USPAT; US-PGPUB	2004/09/10 17:19
-	215	((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or SixNy) same ((rapid adj thermal adj ((chemical adj vapor adj deposit\$3) or CVD)) or (remote adj plasma adj enhanced adj ((chemical adj vapor adj deposit\$3) or CVD)) or (atomic adj layer adj ((chemical adj vapor adj deposit\$3) or CVD)))	USPAT; US-PGPUB	2004/09/10 17:34

-	0	((silicon adj nitride) or "Si.sub.3N.sub.4" or	USPAT;	2004/09/10
		Si3N4 or "Si.sub.xN.sub.y" or SixNy) same (rapid	US-PGPUB	17:35
		adj thermal adj ((chemical adj vapor adj		
		deposit\$3) or CVD)) same (remote adj plasma adj		
		enhanced adj ((chemical adj vapor adj		
		deposit\$3) or CVD)) same (atomic adj layer adj ((
		chemical adj vapor adj deposit\$3) or CVD))		
-	1822	atomic adj layer adj deposit\$3	USPAT;	2004/09/10
			US-PGPUB	17:35
-	0	((silicon adj nitride) or "Si.sub.3N.sub.4" or	USPAT;	2004/09/10
		Si3N4 or "Si.sub.xN.sub.y" or SixNy) same (rapid	US-PGPUB	17:35
		adj thermal adj ((chemical adj vapor adj		
		deposit\$3) or CVD)) same (remote adj plasma adj		
		enhanced adj ((chemical adj vapor adj		
		deposit\$3) or CVD)) same (atomic adj layer adj		
		deposit\$3)		
-	4	((silicon adj nitride) or "Si.sub.3N.sub.4" or	USPAT;	2004/09/10
		Si3N4 or "Si.sub.xN.sub.y" or SixNy) same (rapid	US-PGPUB	17:39
		adj thermal adj ((chemical adj vapor adj		
		deposit\$3) or CVD)) same (remote adj plasma adj		
		enhanced adj ((chemical adj vapor adj		
		deposit\$3) or CVD))		
-	74	1 11	USPAT;	2004/09/10
		Si3N4 or "Si.sub.xN.sub.y" or SixNy) same	US-PGPUB	18:30
		(remote adj plasma adj enhanced adj ((chemical		
		adj vapor adj deposit\$3) or CVD))		
-	265	((silicon adj nitride) or "Si.sub.3N.sub.4" or	USPAT;	2004/09/10
		Si3N4 or "Si.sub.xN.sub.y" or SixNy) same	US-PGPUB	18:30
		((atomic adj layer adj ((chemical adj vapor adj		
		deposit\$3) or CVD)) or (atomic adj layer adj		
		deposit\$3))		

L	Hits	Search Text	DB	Time stamp
Number				
1	136406	silicon adj \$2oxide	USPAT;	2004/09/10
			US-PGPUB	19:54
2	134116	"SiO.sub.2"	USPAT;	2004/09/10
			US-PGPUB	19:54
3	6905	SiO2	USPAT;	2004/09/10
			US-PGPUB	19:55
4	23545	thermal adj oxidation	USPAT;	2004/09/10
			US-PGPUB	19:55
5	1234	plasma adj oxidation	USPAT;	2004/09/10
			US-PGPUB	19:55
6	102	((silicon adj \$2oxide) or "SiO.sub.2" or SiO2)	USPAT;	2004/09/10
		same (thermal adj oxidation) same (plasma adj	US-PGPUB	19:56
		oxidation)		